



## MM54HC283/MM74HC283 4-Bit Binary Adder with Fast Carry

### General Description

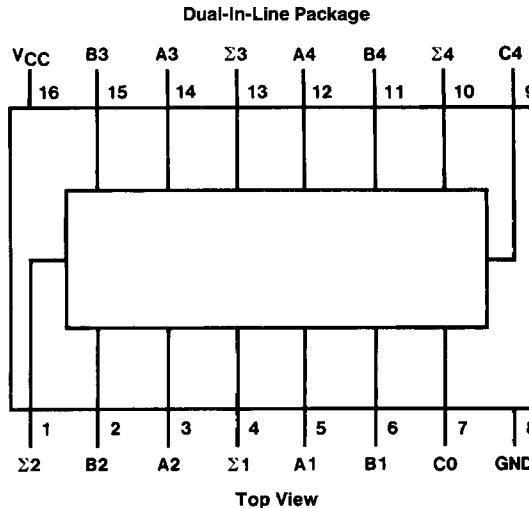
This full adder performs the addition of two 4-bit binary numbers utilizing advanced silicon-gate CMOS technology. The sum ( $\Sigma$ ) outputs are provided for each bit and the resultant carry ( $C_4$ ) is obtained from the fourth bit. These adders feature full internal look ahead across all four bits. This provides the system designer with partial look-ahead performance at the economy and reduced package count of a ripple-carry implementation.

The adder logic, including the carry, is implemented in its true form meaning that the end-around carry can be accomplished without the need for logic or level inversion. All inputs are protected from damage due to static discharge by internal diode clamps to  $V_{CC}$  and ground.

### Features

- Full-carry look-ahead across the four bits
- Systems achieve partial look-ahead performance with the economy of ripple carry
- Wide supply range: 2V to 6V
- Low quiescent power consumption: 8  $\mu$ A at 25°C
- Low input current: 1  $\mu$ A maximum

### Connection Diagram



TL/F/5332-1

Order Number **MM54HC283\*** or **MM74HC283\***

\*Please look into Section 8, Appendix D for availability of various package types.

**Absolute Maximum Ratings** (Notes 1 & 2)

If Military/Aerospace specified devices are required, contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	-0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	-1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	-0.5 to $V_{CC} + 1.5V$
Clamp Diode Current ( $I_{HK}, I_{OK}$ )	$\pm 20$ mA
DC Output Current, per pin ( $I_{OUT}$ )	$\pm 25$ mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	$\pm 50$ mA
Storage Temperature Range ( $T_{STG}$ )	-65°C to +150°C
Power Dissipation ( $P_D$ ) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature ( $T_L$ ) (Soldering 10 seconds)	260°C

**Operating Conditions**

		Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V	
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V	
Operating Temp. Range ( $T_A$ )				
MM74HC	-40	+85	°C	
MM54HC	-55	+125	°C	
Input Rise or Fall Times ( $t_r, t_f$ )				
$V_{CC} = 2.0V$	1000	ns		
$V_{CC} = 4.5V$	500	ns		
$V_{CC} = 6.0V$	400	ns		

**DC Electrical Characteristics** (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		<b>74HC</b>	<b>54HC</b>	Units
				Typ	Guaranteed Limits			
$V_{IH}$	Minimum High Level Input Voltage		2.0V	1.5	1.5		1.5	V
			4.5V	3.15	3.15		3.15	V
			6.0V	4.2	4.2		4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V	0.5	0.5		0.5	V
			4.5V	1.35	1.35		1.35	V
			6.0V	1.8	1.8		1.8	V
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V	4.2	3.98	3.84	3.7	V
			6.0V	5.7	5.48	5.34	5.2	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		$\pm 0.1$	$\pm 1.0$	$\pm 1.0$	$\mu A$
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		8.0	80	160	$\mu A$

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of  $5V \pm 10\%$  the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}, I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

**AC Electrical Characteristics**  $V_{CC} = 5V$ ,  $T_A = 25^\circ C$ ,  $C_L = 15 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$ 

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 1$ or $\Sigma 2$		18	27	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 3$		18	27	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 4$		20	30	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From A1 or B1 to $\Sigma 1$		17	26	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to C4		22	32	ns
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From A1 or B1 to C4		22	32	ns

**AC Electrical Characteristics**  $C_L = 50 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$  (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 1$ or $\Sigma 2$		2.0V	60	150	188	225	ns
			4.5V	21	30	37	45	
			6.0V	18	26	32	39	
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 3$		2.0V	60	150	188	225	ns
			4.5V	21	30	37	45	
			6.0V	18	26	32	39	
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to $\Sigma 4$		2.0V	65	162	202	243	ns
			4.5V	24	34	43	51	
			6.0V	19	28	35	42	
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From A1 or B1 to $\Sigma 1$		2.0V	60	150	188	225	ns
			4.5V	22	33	41	50	
			6.0V	18	27	34	41	
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From C0 to C4		2.0V	70	175	219	263	ns
			4.5V	26	39	49	59	
			6.0V	21	32	40	46	
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay From A1 or B1 to C4		2.0V	70	175	219	263	ns
			4.5V	26	39	49	59	
			6.0V	21	32	40	46	
$t_{THL}, t_{TLH}$	Maximum Output Rise and Fall Time		2.0V	28	75	95	110	ns
			4.5V	8	15	19	22	
			6.0V	7	13	16	19	
$C_{IN}$	Maximum Input Capacitance			6	10	10	10	pF
$C_{PD}$	Power Dissipation Capacitance (Note 5)			150				pF

Note 5:  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

## Truth Table

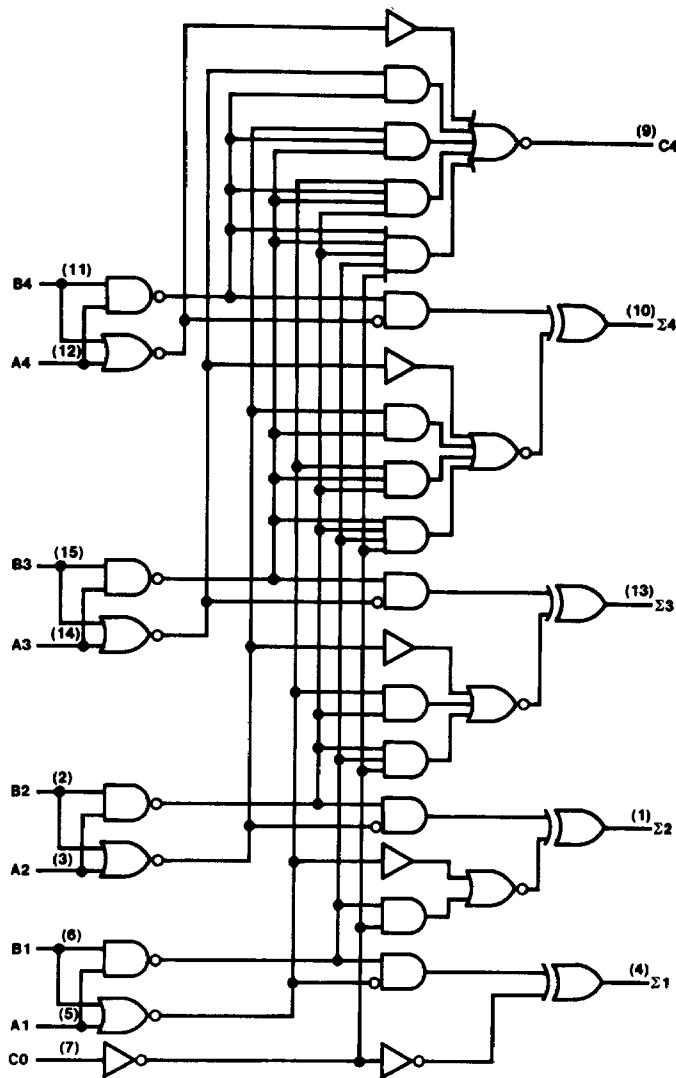
Input								Output												
								When C0 = L				When C0 = H								
When C2 = L				When C2 = H				When C2 = L				When C2 = H								
A1	A3	B1	B3	A2	A4	B2	B4	$\Sigma_1$	$\Sigma_3$	$\Sigma_2$	$\Sigma_4$	C2	C4	$\Sigma_1$	$\Sigma_3$	$\Sigma_2$	$\Sigma_4$	C2	C4	
L	H	L	H	L	L	L	L	L	H	L	L	L	L	L	H	L	H	L	H	L
H	L	H	L	H	H	H	H	H	L	H	H	H	H	H	L	H	H	H	L	H
L	H	L	H	L	L	L	L	L	H	L	L	L	L	L	H	L	H	L	H	L
H	L	H	L	H	H	H	H	H	L	H	H	H	H	H	L	H	H	H	L	H
L	H	L	H	L	L	L	L	L	H	L	L	L	L	L	H	L	H	L	H	L
H	L	H	L	H	H	H	H	H	L	H	H	H	H	H	L	H	H	H	L	H

H = high level, L = low level

**Note:** Input conditions at A1, B1, A2, B2, and C0 are used to determine outputs  $\Sigma_1$  and  $\Sigma_2$  and the value of the internal carry C2. The values at C2, A3, B3, A4, and B4 are then used to determine outputs  $\Sigma_3$ ,  $\Sigma_4$ , and C4

## Logic Diagram

'HC283



TL/F/5332-2